



2mm InGaAs PIN PD

(P/N.: InGaAs-2000-01)

Features

- 2mm active area (square)
- Low dark current and high responsivity

Absolute Maximum Ratings

Parameter	Symbol	Min	Typ	Max	Unit
Operating Case Temperature	T _C	-40	-	85	°C
Storage Temperature	T _{STG}	-40	-	125	°C
Lead Soldering Temperature	T _{SOL}	-	-	260 (10s)	°C
Reverse voltage	V _R			20	V

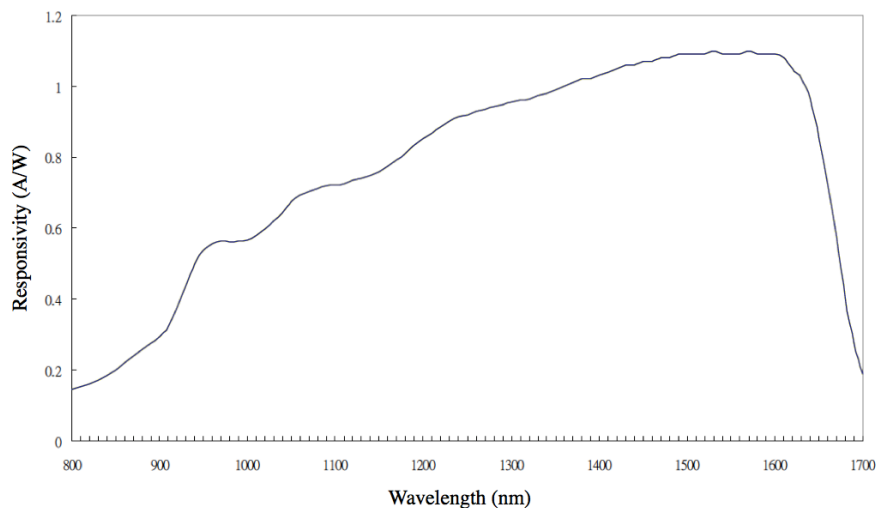
Opto-Electrical Characteristics

V_R = 5V, 25 °C

Parameter	Symbol	Min	Typ	Max	Unit
Active area (square)		-	2000	-	μm
Wavelength range	λ	800	-	1700	nm
1310nm Responsivity	R	0.9	0.95	-	A/W
1550nm Responsivity		0.95	1.0	-	A/W
Capacitance @ f = 1MHz		-	130	220	pF
Dark current	I _D	-	2	5	nA
Rise time	t _R	-	-	10	μs
Breakdown voltage	V _B	20	-	-	V

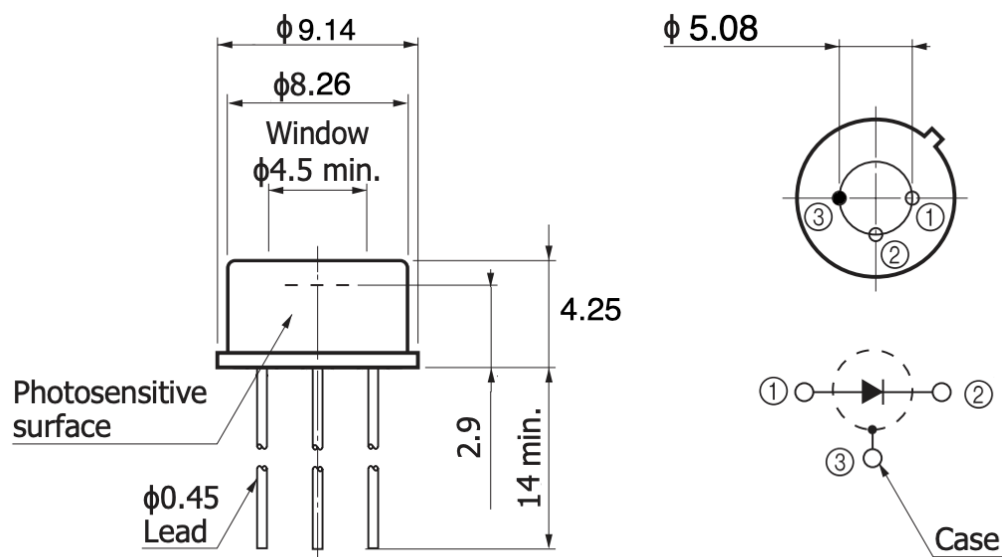
Typical Performance at 25°C

InGaAs die responsivity only



Dimensional outlines (unit = mm)

TO



Package can be customized or modified to SMD